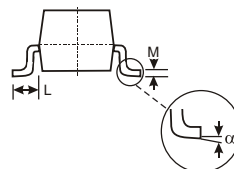
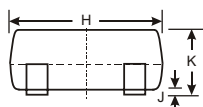
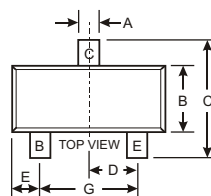


Features

- High Collector Current
- PNP complement:S9012
- Excellecnt h_{FE} Linearity
- Marking Code:J3

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

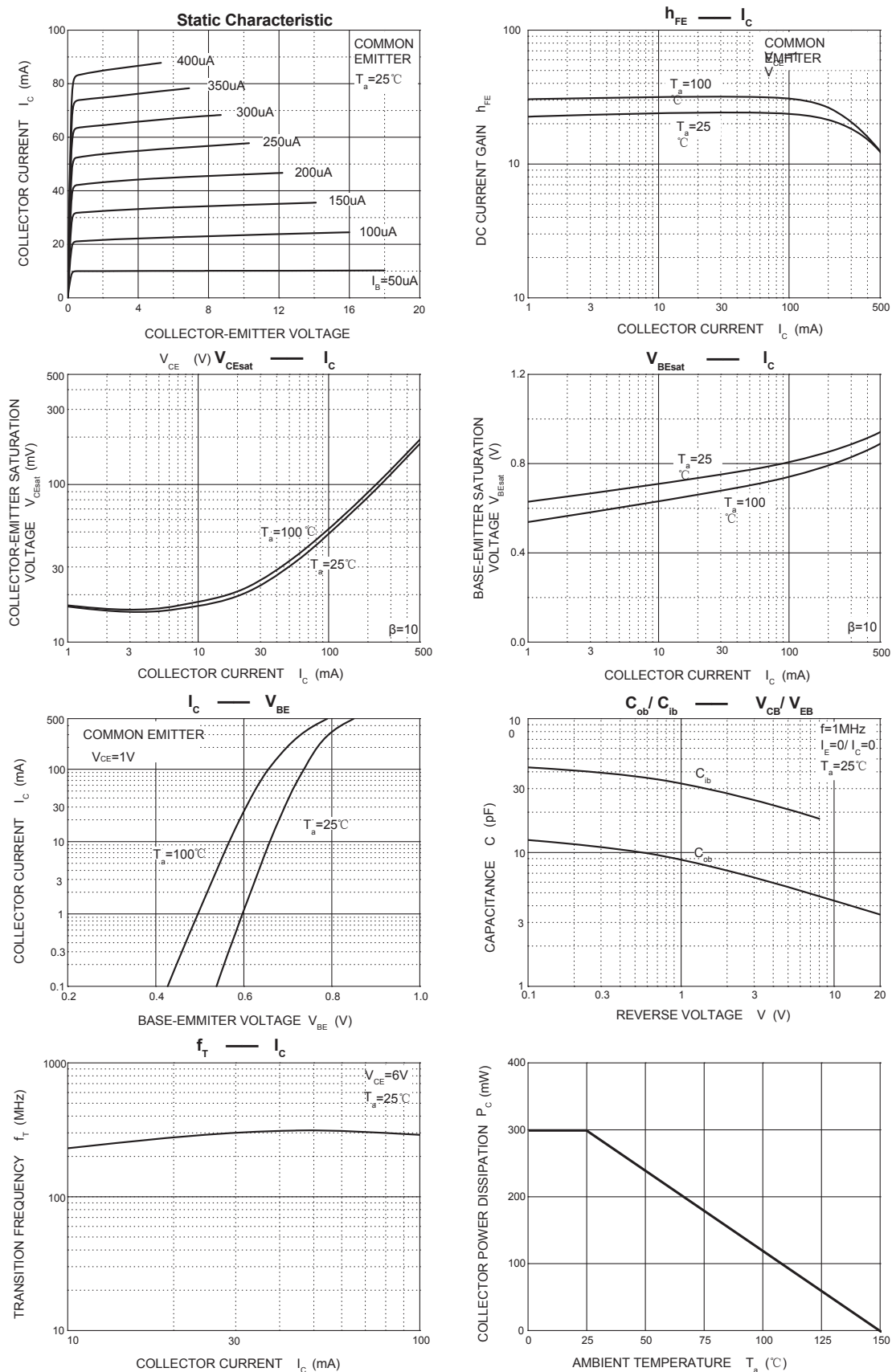
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}$, $I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20\text{V}$, $I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}$, $I_C=50\text{mA}$	120		400	
	$h_{FE(2)}$	$V_{CE}=1\text{V}$, $I_C=500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}$, $I_B=50\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500\text{mA}$, $I_B=50\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=6\text{V}$, $I_C=20\text{mA}$, $f=30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=6\text{V}$, $I_E=0$, $f=1\text{MHz}$			8	pF

CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H	J
RANGE	120-200	200-350	300-400

TYPICAL TRANSIENT CHARACTERISTICS



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